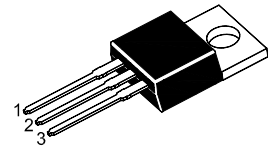


2SB2955

PNP Epitaxial Silicon Power Transistor

for power switching circuits and general-purpose amplifiers.



1.Base 2.Collector 3.Emitter
TO-220 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	70	V
Collector Emitter Voltage	$-V_{CEO}$	60	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	10	A
Base Current	$-I_B$	6	A
Power Dissipation ($T_C \leq 25\text{ }^\circ\text{C}$)	P_{tot}	75	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 4\text{ V}$, $-I_C = 4\text{ A}$ at $-V_{CE} = 4\text{ V}$, $-I_C = 10\text{ A}$	h_{FE} h_{FE}	20 5	- -	70 -	- -
Collector Base Cutoff Current at $-V_{CB} = 70\text{ V}$ at $-V_{CB} = 70\text{ V}$, $T_C = 150\text{ }^\circ\text{C}$	$-I_{CBO}$	- -	- -	1 10	mA
Collector Emitter Cutoff Current at $-V_{CE} = 30\text{ V}$	$-I_{CEO}$	-	-	0.7	mA
Emitter Base Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	-	5	mA
Collector Emitter Sustaining Voltage at $-I_C = 0.2\text{ A}$	$-V_{CEO(sus)}$	60	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 4\text{ A}$, $-I_B = 0.4\text{ A}$ at $-I_C = 10\text{ A}$, $-I_B = 3.3\text{ A}$	$-V_{CE(sat)}$	- -	- -	1.1 8	V
Base Emitter on Voltage at $-V_{CE} = 4\text{ V}$, $-I_C = 4\text{ A}$	$-V_{BE(on)}$	-	-	1.8	V
Transition Frequency at $-V_{CB} = 10\text{ V}$, $-I_C = 0.5\text{ A}$, $f = 500\text{ KHz}$	f_T	2	-	-	MHz

TOP DYNAMIC



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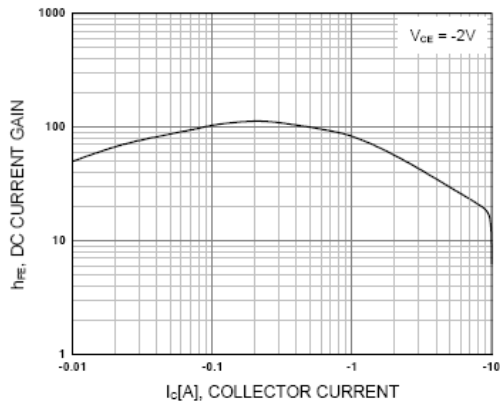


Figure 1. DC current Gain

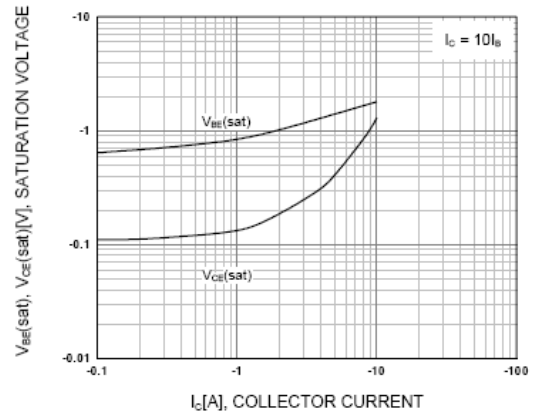


Figure 2. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

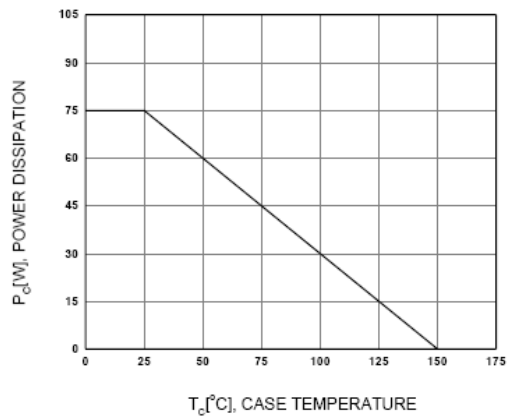
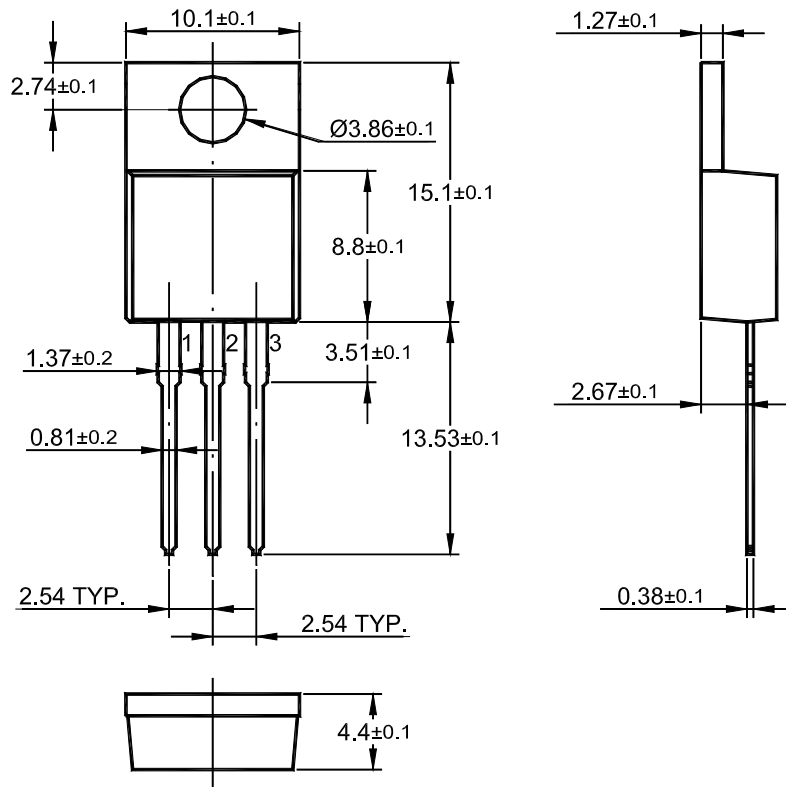


Figure 3. Power Derating

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TO-220 PACKAGE OUTLINE



Dimensions in mm

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